# **CETC** 中电国基南方集团有限公司

# WS3A002120E Silicon Carbide Schottky Diode

#### Features

- Zero Reverse Recovery Current
- Zero Forward Recovery Voltage
- Positive Temperature Coefficient on V<sub>F</sub>
- Temperature-independent Switching
- 175°C Operating Junction Temperature

#### **Benefits**

- Replace Bipolar with Unipolar Device
- Reduction of Heat Sink Size
- Parallel Devices Without Thermal Runaway
- Essentially No Switching Losses

#### **Applications**

- Switch Mode Power Supplies
- Power Factor Correction
- Motor drive, PV Inverter, Wind Power Station

V <sub>RRM</sub>	=	1200	V
I <sub>F</sub> ( T <sub>C</sub> ≤135℃)	=	5	А
Qc	=	8	nC

#### Package





TO-252



Part Number	Package	Marking
WS3A002120E	TO-252	WS3A002120E

## Maximum Ratings

Symbol	Parameter	Value	Unit	Test Conditions	Note
V <sub>RRM</sub>	Repetitive Peak Reverse Voltage	1200	V	$T_{C} = 25^{\circ}C$	
V <sub>RSM</sub>	Surge Peak Reverse Voltage	1200	V	$T_{\rm C} = 25^{\circ}{\rm C}$	
V <sub>R</sub>	DC Blocking Voltage	1200	V	$T_C = 25^{\circ}C$	
lF	Forward Current	10 5 2	A	T <sub>C</sub> ≤ 25°C T <sub>C</sub> ≤ 135°C T <sub>C</sub> ≤ 160°C	
I <sub>FSM</sub>	Non-Repetitive Forward Surge Current	20	А	$T_C$ = 25 $^\circ\text{C}$ , $t_p$ = 8.3ms, Half Sine Wave	
P <sub>tot</sub>	Power Dissipation	58	W	$T_C = 25^{\circ}C$	Fig.3
T <sub>C</sub>	Maximum Case Temperature	155	°C		
T <sub>J</sub> , T <sub>STG</sub>	Operating Junction and Storage Temperature	-55 to 175	°C		



### **Electrical Characteristics**

Symbol	Parameter	Тур.	Max.	Unit	Test Conditions	Note	
M	Forward Voltage	1.55	1.8	V	$I_F = 2A, T_J = 25^{\circ}C$	Fig.1	
V <sub>F</sub>	T Ofward Voltage	2.2	2.5	v	$I_F=2A,T_J=175^\circ C$	1 ig. i	
	Reverse Current	1	20		$V_{R} = 1200V, T_{J} = 25^{\circ}C$	Fig.2	
I <sub>R</sub>		8	200	μA	$V_R = 1200V, T_J = 175^{\circ}C$	1 iy.z	
		135			$V_R = 0V, T_J = 25^{\circ}C, f = 1MHz$		
С	Total Capacitance	11	/	pF	$V_R = 400V, T_J = 25^{\circ}C, f = 1MHz$	Fig.5	
		8			$V_R = 800V, T_J = 25^{\circ}C, f = 1MHz$		
0	Total Capacitive Charge		,		$V_{R} = 800V, I_{F} = 2A$	Fig.4	
Qc	Total Capacitive Charge	8	/	nC	di/dt = 200A/µs, T <sub>J</sub> = 25°C	Fig.4	

### **Thermal Characteristics**

Symbol	Parameter	Тур.	Unit	Note
R <sub>θJC</sub>	Thermal Resistance from Junction to Case	2.55	°C/W	Fig.6
R <sub>0JA</sub>	Thermal Resistance from Junction to Ambient	80	°C/W	
T <sub>sold</sub>	Soldering Temperature	260	°C	

# **Typical Performance**

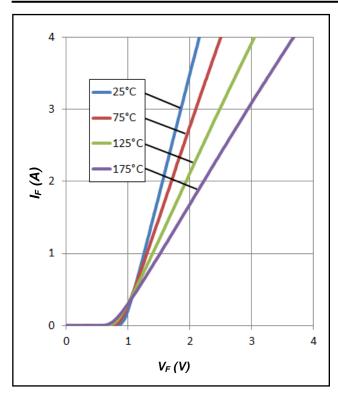
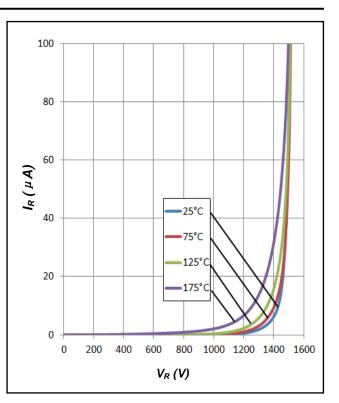


Figure 1. Forward Characteristics



#### Figure 2. Reverse Characteristics



# **Typical Performance**

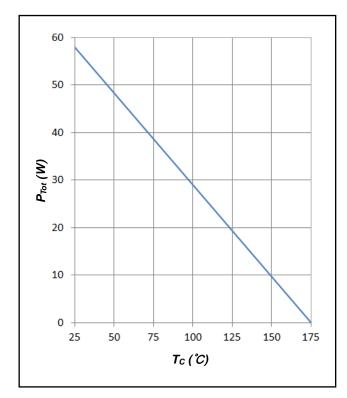


Figure 3. Power Derating

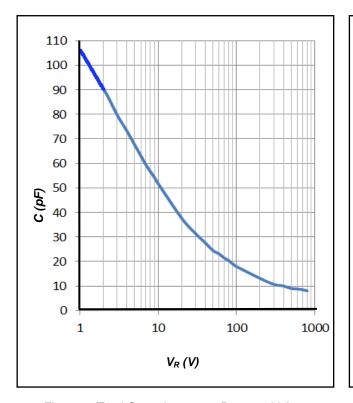


Figure 5. Total Capacitance vs. Reverse Voltage

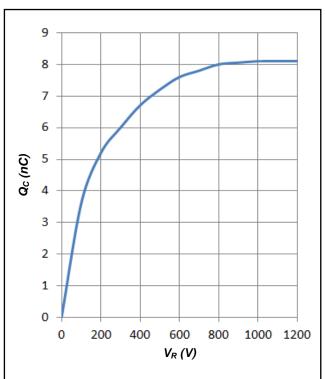
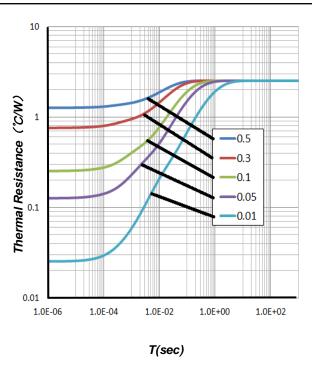
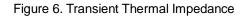


Figure 4. Total Capacitive Charge vs. Reverse Voltage

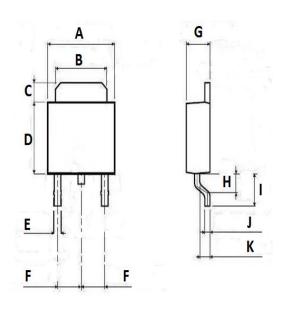




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## **Package Dimensions**

Package TO-252

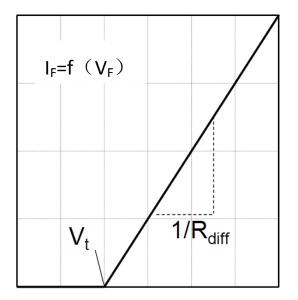


PIN 1	0	
PIN 2		

Symbol	Min. (mm)	Typ. (mm)	Max. (mm)
А	6.3	6.5	6.7
В	5.2	5.3	5.4
С	1.15	1.25	1.35
D	5.7	5.9	6.1
E	0.65	0.7	0.75
F	2.1	2.3	2.5
G	2.2	2.3	2.4
Н	1.45	1.5	1.55
I	2.9	3.0	3.1
J	0.45	0.5	0.55
К	0.9	1	1.1

### **Simplified Diode Model**

#### Equivalent IV Curve for Model



#### **Mathematical Equation**

$$V_F = V_t + I_F \times R_{diff}$$

$$\begin{split} V_t &= -0.0012 \textbf{x} T_j + 1.0 \ [V] \\ R_{diff} &= 7.05 \textbf{x} 10^{-6} \textbf{x} T_j^2 + 1.42 \textbf{x} 10^{-3} \textbf{x} T_j + 0.26 \ [\Omega] \end{split}$$

Note:

 $\label{eq:time_state} \begin{array}{l} Tj = Diode \mbox{ Junction Temperature In Degrees Celsius,} \\ \mbox{valid from 25°C to 175°C} \\ I_{F}\mbox{=} \mbox{ Forward Current} \\ \mbox{ Less than 4A} \end{array}$ 

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